

ABSTRACT OF THE DISCLOSURE

A nitride compound semiconductor element having improved characteristics, productivity and yield. A nitride compound semiconductor element comprises: a sapphire substrate; a first single crystalline layer of AlN formed on said sapphire substrate; a second single crystalline layer formed on said first single crystalline layer, said second single crystalline layer being made of  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0.8 \leq x \leq 0.97$ ) and having a thickness of equal to or more than  $0.3 \mu\text{m}$  and equal to or less than  $6 \mu\text{m}$ ; and a device structure section of a nitride semiconductor formed on said second single crystalline layer.